650V/ 4A Silicon Carbide Power Schottky Barrier Diode

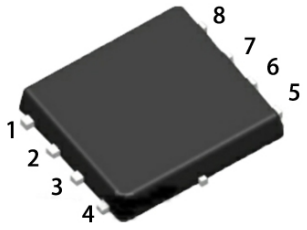
Features

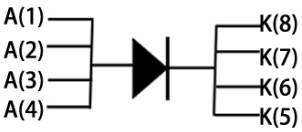
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

Key Characteristics		
V_{RRM}	650	V
I_F, $T_c \leqslant 158℃$	4	A
Q_C	11	nC

Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements





Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV

Part No.	Package Type	Marking
G5S6504Z	DFN5*6	G5S6504Z

Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		650	V
Surge Peak Reverse Voltage	V_{RSM}		650	V
DC Blocking Voltage	V_{DC}		650	V
Continuous Forward Current	I_F	T_C=25℃ T_C=125℃ T_C=158℃	15.45 8.45 4	A
Repetitive Peak Forward Surge Current	I_{FRM}	T_C=25℃, tp=10ms， Half Sine Wave，D=0.3	20	A
Non-repetitive Peak Forward Surge Current	I_{FSM}	T_C=25℃, tp=10ms， Half Sine Wave	35	A
Power Dissipation	P_{TOT}	T_C=25℃	84	W
		T_C=110℃	37	W
Operating Junction	T_j		-55℃ to 175℃	℃
Storage Temperature	T_{stg}		-55℃ to 175℃	℃

Thermal Characteristics

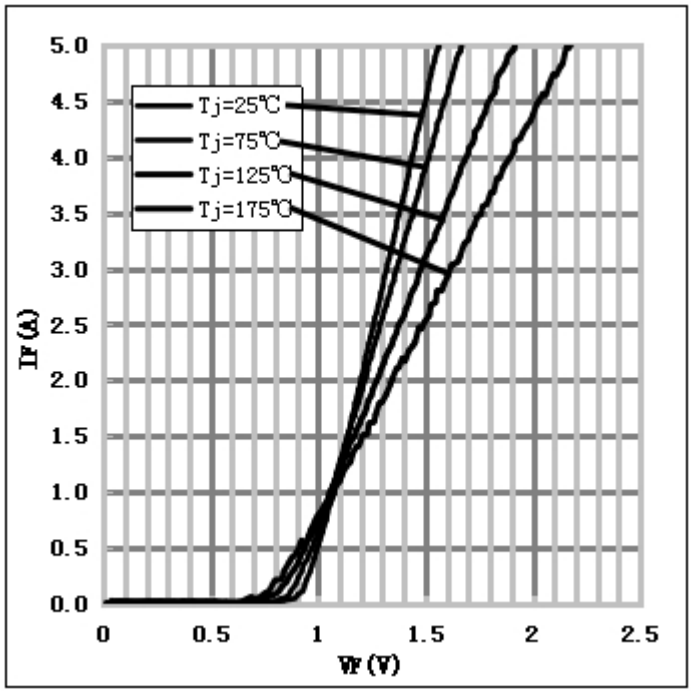
Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	$R_{th\ JC}$		1.78	℃/W

Electrical Characteristics

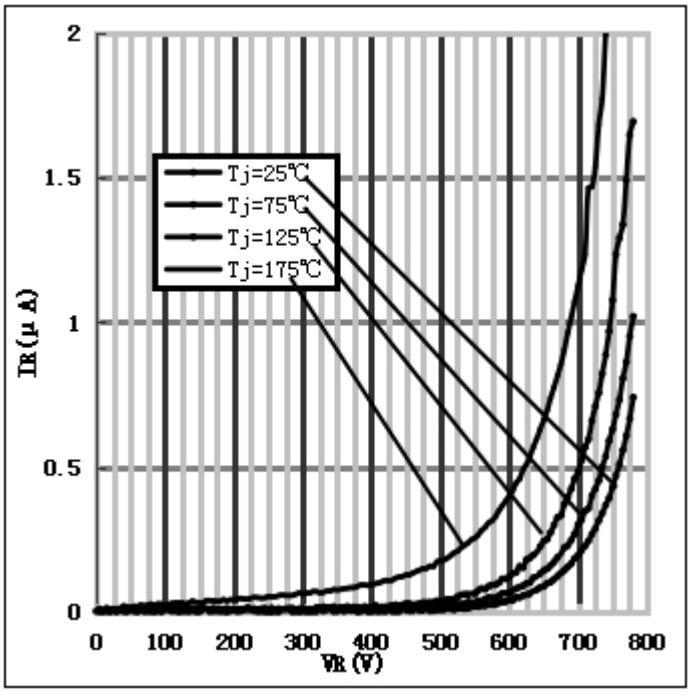
Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	V_F	I_F=4A, T_j=25℃	1.4	1.6	V
		I_F=4A, T_j=175℃	1.9	2.5	
Reverse Current	I_R	V_R=650V, T_j=25℃	0.07	50	μA
		V_R=650V, T_j=175℃	0.65	100	
Total Capacitive Charge	Q_C	V_R=400V, T_j=150℃ $Qc = \int_0^{VR} C(V)dV$	11	-	nC
Total Capacitance	C	V_R=0V, T_j=25℃, f=1MHZ	181	220	pF
		V_R=200V, T_j=25℃, f=1MHZ	22.5	25	
		V_R=400V, T_j=25℃, f=1MHZ	20.5	21	

Performance Graphs

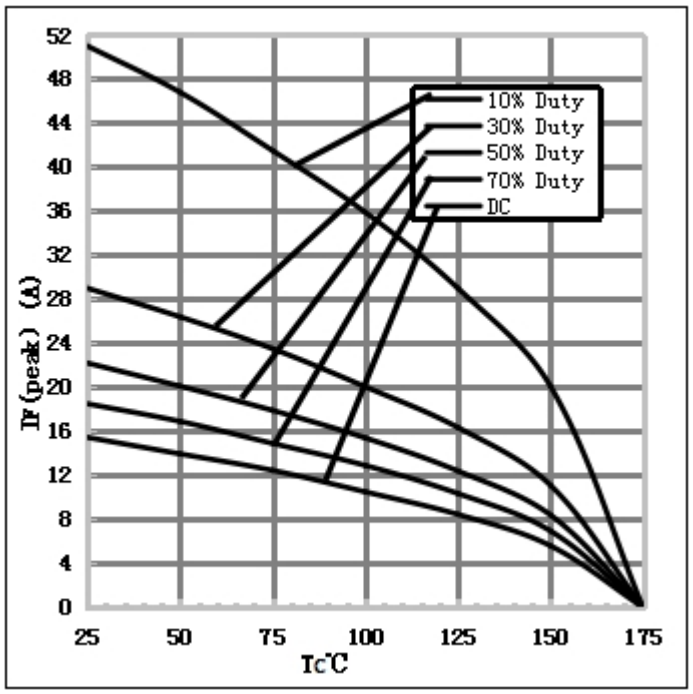
1) Forward IV characteristics as a function of Tj :



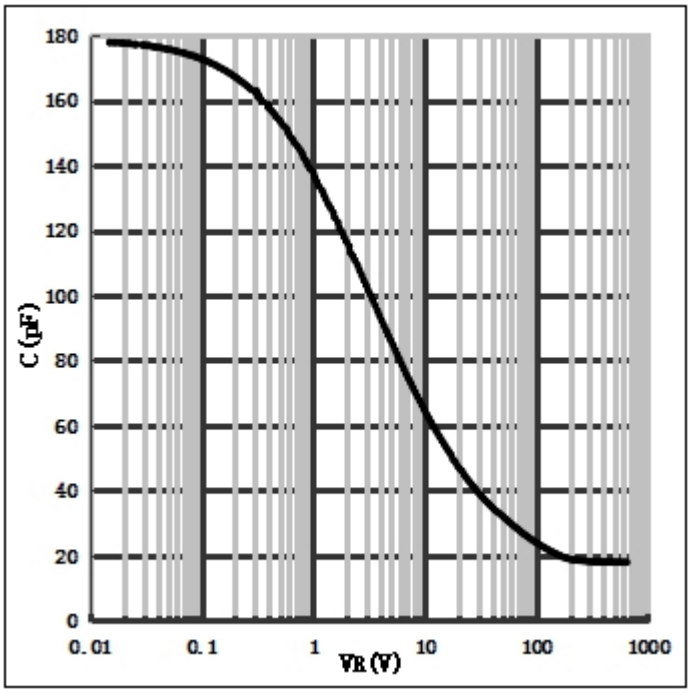
2) Reverse IV characteristics as a function of Tj :



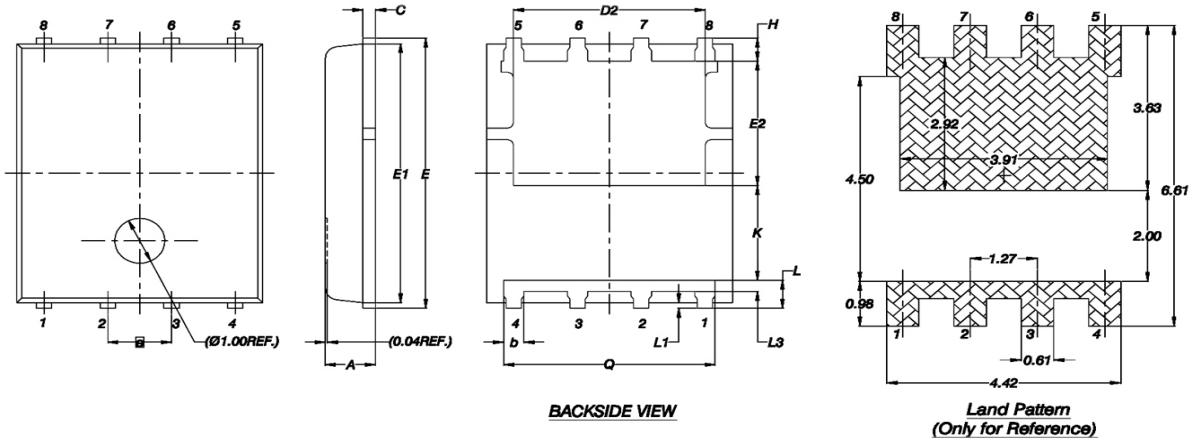
3) Current Derating:



4) Capacitance vs. reverse voltage:



Package DFN5*6



单位：mm

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	---	0.05
b	0.33	0.41	0.51
c	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	2.66	2.76	2.86
e	1.27 BSC		
H	0.41	0.51	0.61
K	2.00	2.10	2.20
L	0.53	0.63	0.73
L1	0.06	0.13	0.20
L3	0.15	0.25	0.35
Q	4.12	4.22	4.32
α	0°	-	12°

Note:
1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs.
   Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic
   Body Exclusive Of Mold Flash, Tie Bar , Tie Bar Burrs, Gate Burrs And Interlead Flash,
   But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
4. The Package Top May Be Smaller Than The Package Bottom.

Note: The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2). RoHS Certification and other certifications can be obtained from GPT sales representatives or GPT website: http://globalpowertech.cn/English/index.asp

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